#### CXSH-4

# SURFACE MOUNT SILICON SCHOTTKY RECTIFIER



www.centralsemi.com

### **DESCRIPTION:**

The CENTRAL SEMICONDUCTOR CXSH-4 type is a Schottky barrier rectifier mounted in an epoxy molded case using a metal to silicon junction to yield low forward voltage drop. This device utilizes a single chip with anode connections made to PIN 1 and PIN 3.

**MARKING: FULL PART NUMBER** 



MAXIMUM RATINGS: (T <sub>A</sub> =25°C)	SYMBOL		UNITS
Peak Repetitive Reverse Voltage	$V_{RRM}$	40	V
DC Blocking Voltage	$V_{R}$	40	V
RMS Reverse Voltage	V <sub>R(RMS)</sub>	28	V
Average Forward Current	lo	1.0	Α
Peak Forward Surge Current, tp=8.3ms	<sup>I</sup> FSM	10	Α
Operating and Storage Junction Temperature	$T_J,T_stg$	-65 to +150	°C

# $\textbf{ELECTRICAL CHARACTERISTICS:} \ (T_{\mbox{\scriptsize A}} = 25 \ ^{\circ}\mbox{C unless otherwise noted})$

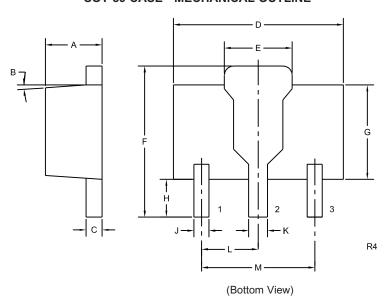
SYMBOL	TEST CONDITIONS	MAX	UNITS
$I_{R}$	V <sub>R</sub> =40V	1.0	mA
$I_{R}$	V <sub>R</sub> =40V, T <sub>A</sub> =100°C	10	mA
VF	I <sub>F</sub> =1.0A	0.55	V

### CXSH-4

### SURFACE MOUNT SILICON SCHOTTKY RECTIFIER



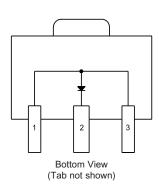
# **SOT-89 CASE - MECHANICAL OUTLINE**



### LEAD CODE:

- 1) Anode 2) Cathode 3) Anode

#### MARKING: FULL PART NUMBER



DIMENSIONS							
	INCHES		MILLIMETERS				
SYMBOL	MIN	MAX	MIN	MAX			
Α	0.055	0.067	1.40	1.70			
В	4°		4°				
С	0.014	0.018	0.35	0.46			
D	0.173	0.185	4.40	4.70			
Е	0.064	0.074	1.62	1.87			
F	0.146	0.177	3.70	4.50			
G	0.090	0.106	2.29	2.70			
Н	0.028	0.051	0.70	1.30			
J	0.014	0.019	0.36	0.48			
K	0.017	0.023	0.44	0.58			
Ĺ	0.059		1.50				
М	0.118		3.00				

SOT-89 (REV: R4)

R7 (19-February 2010)